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Simulation of LHCb silicon strip detector response using a

The charge collection properties of the LHCb n on n silicon Strip detector was modelled using the DIOS and DESSIS Packages from the ISE/synopsys program suite. The detector response to MIPS was modelled in detail as a function Of applied bias voltage, radiation damage and incident track angle. a centroid shift in the collected charge between positive and Negative incident track angles has been predicted and operational Bias voltages deduced.

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Track Classification: Pixel Detectors for Charged Particles